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adjusting the temperature of said semiconductor wafer to a predetermined temperature according to a predetermined heat cycle, said predetermined heat cycle including a heating stage;

during at least one stage of said predetermined heat cycle, providing a gas to selectively control the temperature of at least one of said localized regions of said semiconductor wafer to minimize temperature deviation of said at least one localized region from said predetermined temperature.

B² Sub E3
4. (Amended) A method as defined in claim 1, further comprising the step of controlling the temperature of said gas.

5. (Amended) A method as defined in claim 1, further comprising the step of controlling the flow rate of said gas.

B³ Sub E5
11. (Amended) A method as defined in claim 1, wherein said temperature of said at least one localized region is decreased during said heating stage of said predetermined heat cycle.

B⁴ Sub E7
13. (Amended) A method as defined in claim 12, wherein said temperature of said at least one localized region is increased during said cooling stage of said predetermined heat cycle.

REMARKS

Favorable reconsideration and allowance of the present application in view of the foregoing amendments and following remarks are respectfully requested.

As indicated above, various amendments have been made to claims 1, 4-5, 11,